Ziwu Ji

List of Publications by Year
in descending order

23 papers	463 citations	759233 12 h-index	713466 21 g-index
23 all docs	23 docs citations	23 times ranked	653 citing authors

#	Article	IF	Citations
1	Influence of excitation power and temperature on photoluminescence in InGaN/GaN multiple quantum wells. Optics Express, 2012, 20, 3932.	3.4	142
2	Effect of deposition temperature on transparent conductive properties of Î³-CuI film prepared by vacuum thermal evaporation. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 1466-1470.	1.8	68
3	Influence of the InGaN/GaN quasi-superlattice underlying layer on photoluminescence in InGaN/GaN multiple quantum wells. Physica E: Low-Dimensional Systems and Nanostructures, 2016, 76, 1-5.	2.7	29
4	â€œW-shapedâ€• injection current dependence of electroluminescence linewidth in green InGaN/GaN-based LED grown on silicon substrate. Optics Express, 2017, 25, A871.	3.4	29
5	Electroluminescence properties of InGaN/GaN multiple quantum well-based LEDs with different indium contents and different well widths. Scientific Reports, 2017, 7, 15301.	3.3	27
6	Transfer and recombination mechanism of carriers in phase-separated InGaN quantum wells. Journal of Applied Physics, 2013, 114, .	2.5	23
7	Green and blue emissions in phase-separated InGaN quantum wells. Journal of Applied Physics, 2013, 114, 163525.	2.5	23
8	Fabrication of Non-Stoichiometric Titanium Dioxide by Spark Plasma Sintering and Its Thermoelectric Properties. Materials Transactions, 2012, 53, 1208-1211.	1.2	18
9	Diameter-dependent photoluminescence properties of strong phase-separated dual-wavelength InGaN/GaN nanopillar LEDs. Applied Surface Science, 2017, 410, 196-200.	6.1	15
10	Influence of injection current and temperature on electroluminescence in InGaN/GaN multiple quantum wells. Physica E: Low-Dimensional Systems and Nanostructures, 2014, 59, 56-59.	2.7	13
11	Enhanced localisation effect and reduced quantum-confined Stark effect of carriers in InGaN/GaN multiple quantum wells embedded in nanopillars. Journal of Luminescence, 2018, 203, 216-221.	3.1	13
12	A weak electron transporting material with high triplet energy and thermal stability via a super twisted structure for high efficient blue electrophosphorescent devices. Journal of Materials Chemistry, 2011, 21, 19058.	6.7	12
13	Light Control of Ferromagnetism in ZnO Films on Pt Substrate at Room Temperature. Scientific Reports, 2017, 7, 45642.	3.3	12
14	Fabrication of p-ZnO:Na/n-ZnO:Na homojunction by surface pulsed laser irradiation. RSC Advances, 2017, 7, 37296-37301.	3.6	9
15	Wave-shaped temperature dependence characteristics of the electroluminescence peak energy in a green InGaN-based LED grown on silicon substrate. Scientific Reports, 2020, 10, 129.	3.3	7
16	Photoluminescence properties of InGaN/GaN multiple quantum wells containing a gradually changing amount of indium in each InGaN well layer along the growth direction. Journal of Luminescence, 2020, 223, 117225.	3.1	7
17	Structural properties of Alq3 nanocrystals prepared by physical vapor deposition and facile solution method. International Journal of Modern Physics B, 2015, 29, 1542042.	2.0	5
18	Combined effect of the indium content and well width on electroluminescence in InGaN/GaN multiple quantum well-based LEDs. Materials Express, 2017, 7, 523-528.	0.5	3

#	Article	IF	Citations
19	Effect of InGaN growth interruption on photoluminescence properties of an InGaN-based multiple quantum well structure. Physica E: Low-Dimensional Systems and Nanostructures, 2020, 119, 113982.	2.7	3
20	Effect of low-temperature interlayer in active-region upon photoluminescence in multiple-quantum-well InGaN/GaN. Journal of Luminescence, 2022, 244, 118741.	3.1	3
21	Effects of substrate temperature upon optical properties of ZnTe epilayers grown on (100) GaAs substrates by MOVPE. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 2041-2044.	1.8	1
22	Effect of InGaN well layer growth rate upon photoluminescence of InGaN/GaN multiple-quantum-well structures. , 2022, , 207211.		1
23	Influence of in volatilization on photoluminescence in InGaN/GaN multiple quantum wells. Materials Express, 2021, 11, 2033-2038.	0.5	0